

JIEJIE MICROELECTRONICS CO.

Peak pulse voltage (T _j =25 ; non-repetitive, off-state; FIG.7)	V _{pp}	2.5	kV
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(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit	
I	V _D =12V R _L =33Ω	- -	MAX.	50A	
V		- -	MAX.	1	V
V	V _D =V _{DRM} T _j =125 R _L =3.3kΩ	- -	MIN0.2	V	
I _L	I _G ±.2I _{GT}	-	MAX.	50	mA
				90	
I _H	I _T ±00mA		MAX.	50	mA
dV/dt	V _D =800V Gate Open T _j =125		MIN.	500	V/μs
(dI/dt) _c	(dV/dt) _c =20V/μs, T _j				

t_{on} mA @ CH0 TdARACTERIS.

Year J ST 08 C -1200 BW

FIG.1: Maximum power dissipation versus RMS on-state current

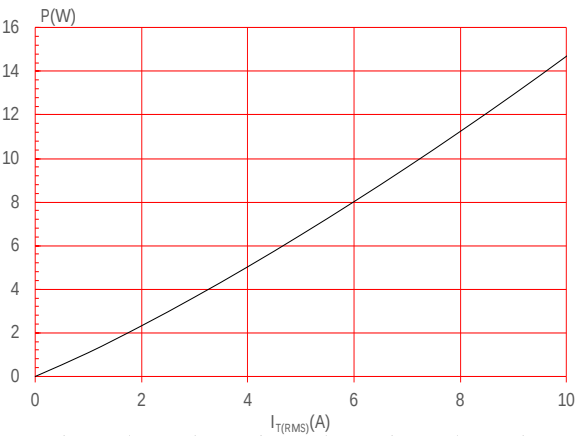


FIG.3: Surge peak on-state current versus number of cycles

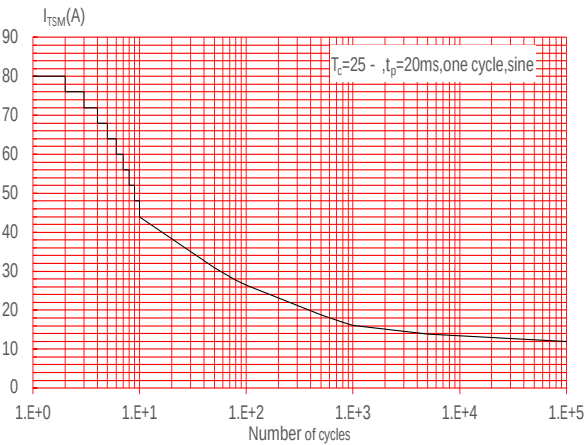


FIG.2: RMS on-state current versus case temperature

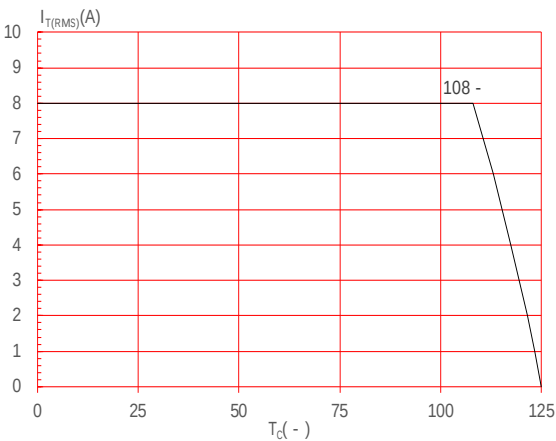


FIG.4: On-state characteristics

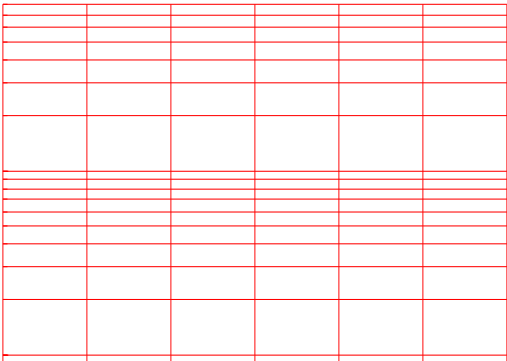
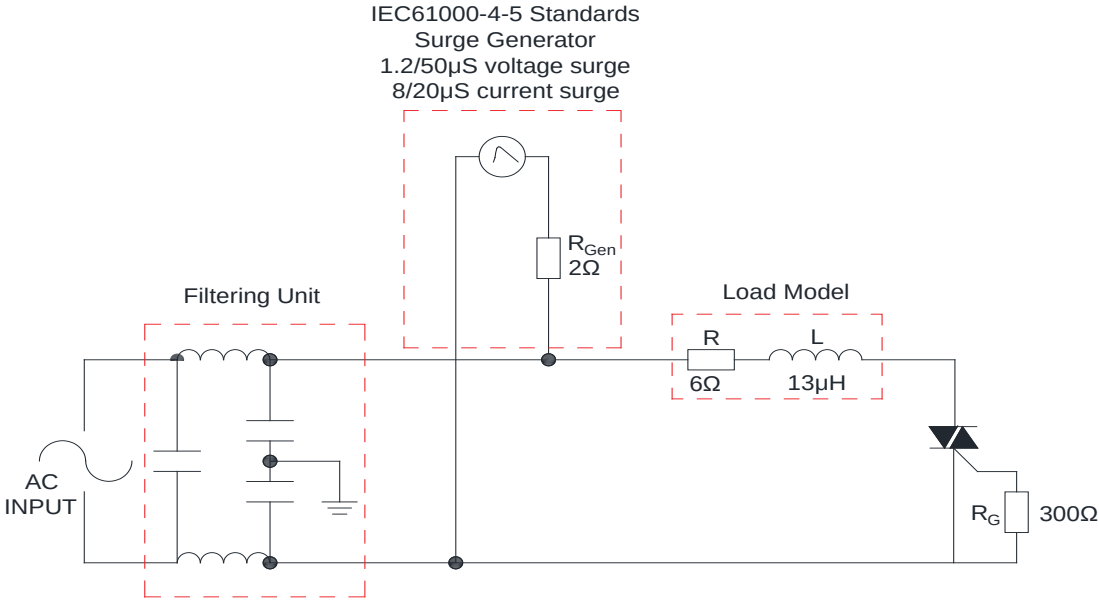


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



JST08C-1200BW



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